

#### **DESCRIPTION**

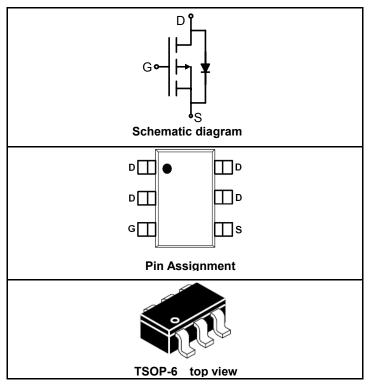
The SSF2449 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

### **GENERAL FEATURES**

- $V_{DS}$  = -20V, $I_{D}$  = -5A  $R_{DS(ON)}$  < 100mΩ @  $V_{GS}$ =-2.5V  $R_{DS(ON)}$  < 60mΩ @  $V_{GS}$ =-4.5V
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

# **Application**

- ●PWM applications
- Load switch
- Power management



#### PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2449	SSF2449	TSOP-6	_		

ABSOLUTE MAXIMUM RATINGS(TA=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	-20	V	
Gate-Source Voltage	V <sub>G</sub> S	±12	V	
Durin Courset Continuous & Courset Duland (Nate 1)	I <sub>D</sub>	-5	Α	
Drain Current-Continuous@ Current-Pulsed (Note 1)	I <sub>DM</sub>	-20	Α	
Maximum Power Dissipation	P <sub>D</sub>	2.0	W	
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	$^{\circ}$	

#### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	R <sub>0JA</sub>	110	°C/W
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**ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)** 

Parameter	Symbol	Condition	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V,V <sub>GS</sub> =0V			-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V			±100	nA



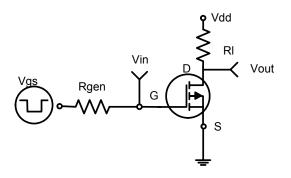
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250μA	-0.6		-1	V
Drain-Source On-State Resistance	В	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-5A		49	60	mΩ
Diam-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-3A		83	100	
Forward Transconductance	<b>G</b> FS	V <sub>DS</sub> =-10V,I <sub>D</sub> =-5A		9		S
DYNAMIC CHARACTERISTICS (Note4)	DYNAMIC CHARACTERISTICS (Note4)					
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =-10V,V <sub>GS</sub> =0V, F=1.0MHz		610		PF
Output Capacitance	Coss			130		PF
Reverse Transfer Capacitance	C <sub>rss</sub>			100		PF
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-10V,I <sub>D</sub> =-5A V <sub>GS</sub> =-4.5V,R <sub>GEN</sub> =1Ω		27		nS
Turn-on Rise Time	t <sub>r</sub>			60		nS
Turn-Off Delay Time	t <sub>d(off)</sub>			30		nS
Turn-Off Fall Time	t <sub>f</sub>			10		nS
Total Gate Charge	Qg	V <sub>DS</sub> =-10V,I <sub>D</sub> =-5A,V <sub>GS</sub> =-4.5V		9.6		nC
Gate-Source Charge	Q <sub>gs</sub>			1.5		nC
Gate-Drain Charge	$Q_{gd}$			2.4		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-1.7A			-1.2	V

## **NOTES:**

- Repetitive Rating: Pulse width limited by maximum junction temperature.
   Surface Mounted on FR4 Board, t ≤ 10 sec.
   Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
   Guaranteed by design, not subject to production testing.



# TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



t<sub>d(on)</sub>

t<sub>on</sub>

t<sub>on</sub>

t<sub>on</sub>

t<sub>on</sub>

t<sub>on</sub>

t<sub>on</sub>

t<sub>on</sub>

t<sub>off</sub>

t<sub>f</sub>

y<sub>0</sub>

INVERTED

10%

PULSE WIDTH

Figure1:Switching Test Circuit

Figure 2:Switching Waveforms

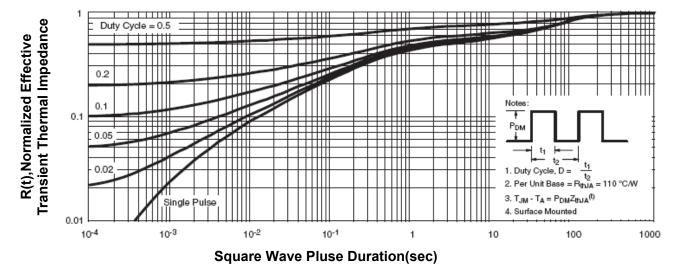
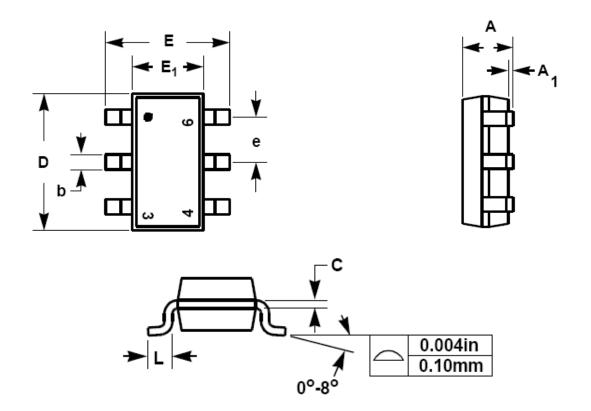
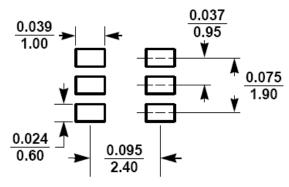


Figure 3: Normalized Maximum Transient Thermal Impedance



# **TSOP-6 PACKAGE INFORMATION**





SYMBOL	Millimeters			
STWIBOL	MIN	MAX		
Α	0.90	1.10		
A1	0.10			
b	0.30	0.50		
С	0.08	0.20		
D	2.70 3.10			
E	2.60	3.00		
E1	1.40	1.80		
е	0.95 BSC			
L	0.35 0.55			

## NOTES:

- 1. Dimensions are inclusive of plating
- 2. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 6 mils.
- 3. Dimension L is measured in gauge plane.
- 4. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.



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